



GP3D012A065A

650V SiC Schottky Diode

Q_C	650 V
I_F	12 A
$T_{j,max}$	175 °C

Amp+™ Features

Thin 2 db 100 ng - fdb d L
 Yc 2 d d d db2 d b d L
 E 1 d d L d hcd d cd L - h bgh f
 bgd L d c 12 7 / 1)
 L L d L d c 12 f d L d L g 604U

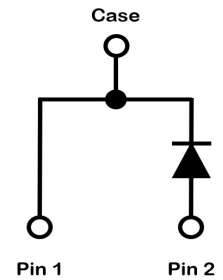
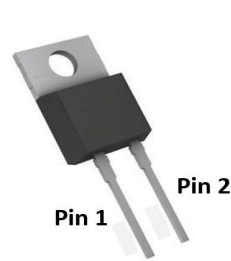
Amp+™ Benefits

Md d 2 - bgh f 2 - -
 Gf gd d b b b
 Qdc bdc gd - h j d h d d L
 D - 12 d

Amp+™ Applications

R h b g 2 c d 2 d - d TCR
 Q2 d e b 12 b2 db 12
 DU bg f h f - L L h -
 N L L d b 12

Package



Part #	Package	Marking
GP3D012A065A	TO-220-2L	3D012A065



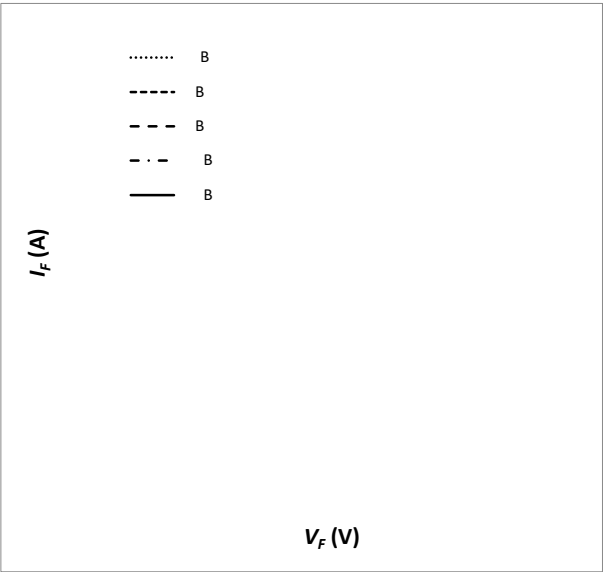
Maximum Ratings

Characteristics	Symbol	Conditions	Values	Unit
B_2 Lh 2 - e c b d L	H_{E1}	S_B 14 B S_1 064 B	31	
		S_B 014 B S_1 064 B	11	
		S_B 04/ B S_1 064 B	03	
R fd 12 , d d h d e c b d L - h d g e d	H_{ERL}	S_B 14 B L 7-2 -	0/ /	
		S_B 00/ B L 7-2 -	8/	
M_2 , d d h d d j e c b d L	H_E	S_B 14 B L 0/ -	74/	
		S_B 14 B L 7-2 -	31	
1 d	$\int^1$	S_B 00/ B L 7-2 -	23	1 -
		S_1 14 B	54/	
Q_d d h d d j d d d 2 L fd	U_{QOL}	S_1 14 B	54/	U
Ch cd f f d c d -		S_1 ,2 - d L d d d h d	1/ /	U. -
Q_2 d ch - h Lh	Q_{21}	S_B 14 B	036	V
N L h f i b 12 - 12 fd L d L d	S_1	B_2 Lh 2 - □	14 064	B
R_2 cd h f Ld d L d		V d - 2 cd h f d c -	15/	B
L_2 Lh f 12 d		L 2 Rb d	0	M



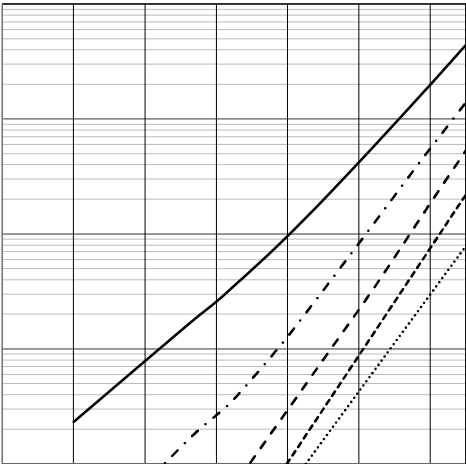
U_C

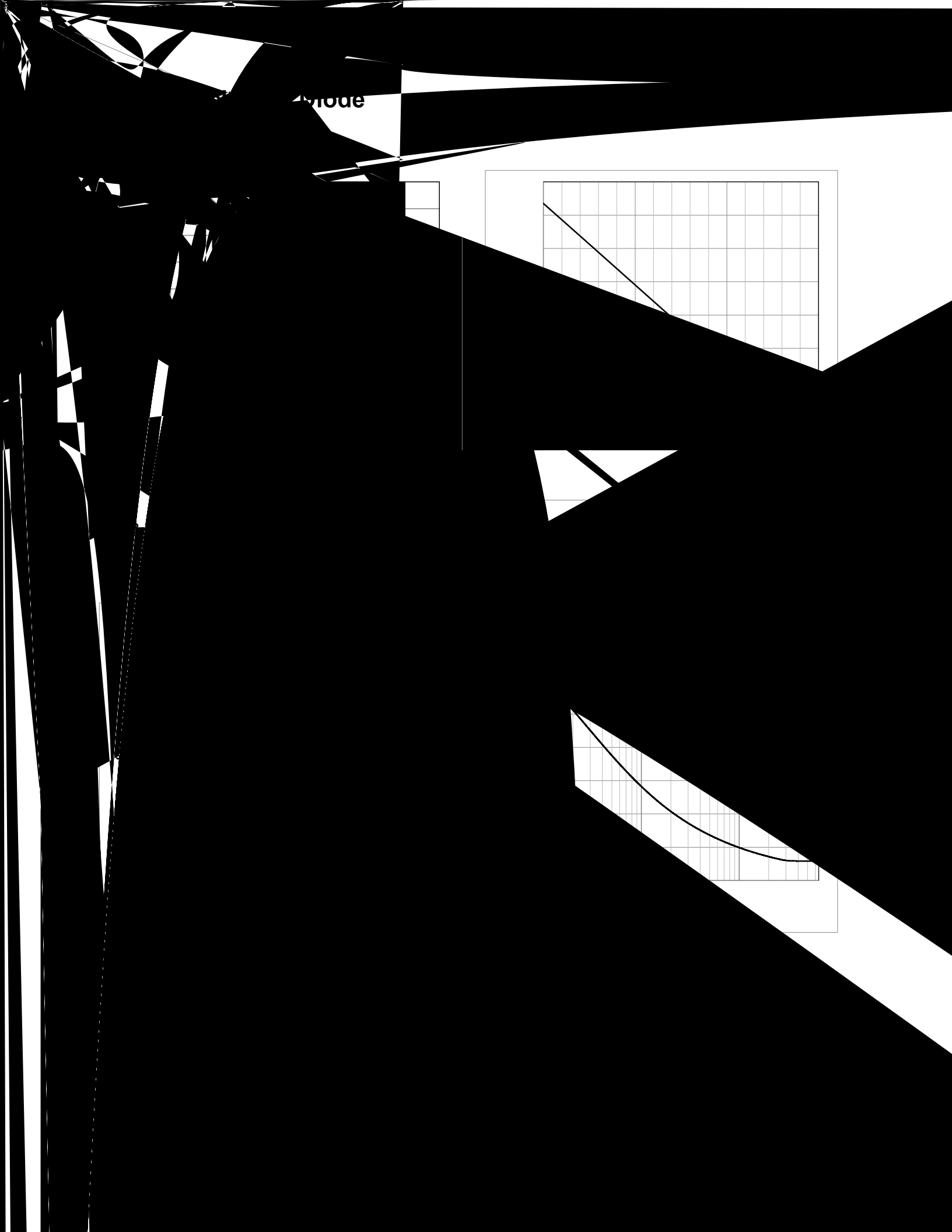
,



⊠
⊠
⊠
⊠

I_R





mode

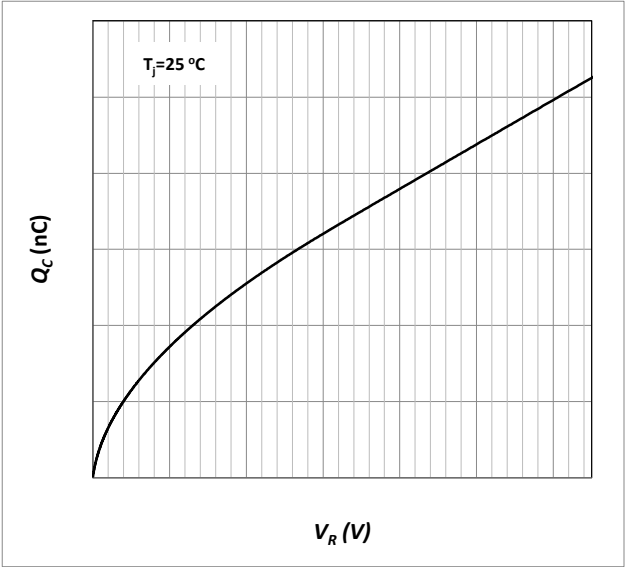


Fig. 7 Capacitive Charge

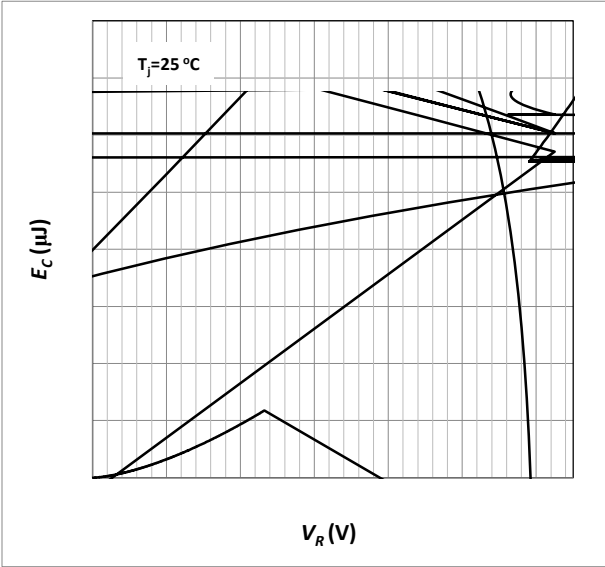


Fig. 8 Typical Capacitance Stored Energy

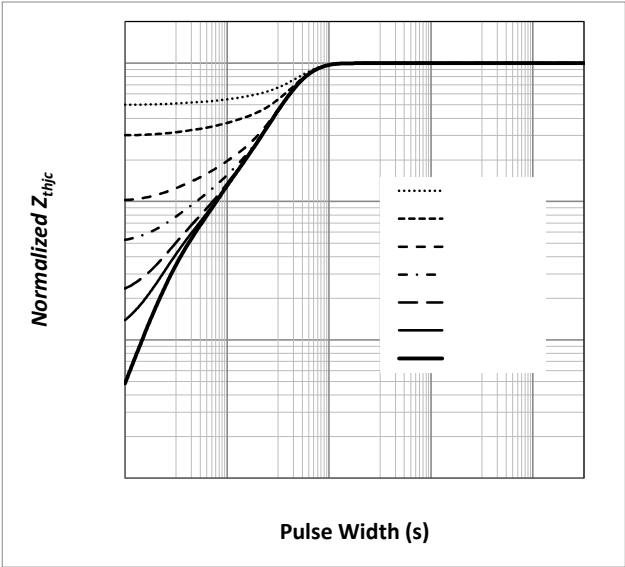


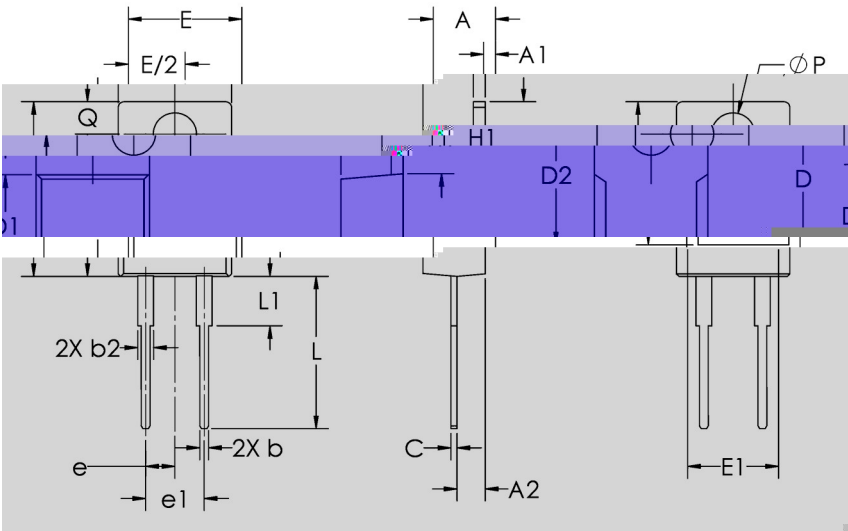
Fig. 9 Transient Thermal Impedance

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Amp+™

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Package Dimensions TO-220-2L



Sym	Millimeters		Inches	
	Min	Max	Min	Max
	3-1/	3-6/	/ -054	/ -074
0	0-03	0-3/	/ -1 34	/ -1 44
1	1-1 2	1-81	/ -1 7/	/ -004
a	/ -27	0-1	/ -1 04	/ -1 3/
a1	0-1	0-67	/ -1 3/	/ -1 6/
b	/ -25	/ -65	/ -1 03	/ -1 2/
C	03-11	05-40	/ -45/	/ -54/
C0	7-27	8-3/	/ -22/	/ -26/
C1	01-08	02-02	/ -37/	/ -406
D	8-54	0/ -56	/ -27/	/ -31/
D0	5-75	7-78	/ -16/	/ -24/
d	1-43 ARB		-0/ / ARB	
d0	4-1 7 ARB		-1/ / ARB	
G0	4-73	5-75	/ -12/	/ -16/
K	01-46	03-62	/ -384	/ -47/
K0	2-5/	5-24	/ -031	/ -14/
O	2-42	3-1 8	/ -028	/ -050
P	1-43	2-32	/ -0/ /	/ -024

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	Qd h h	M ₂ Ld
	0-/	Hh h d d - d 2 ec L - g d L
01.1/.1/ 08	0-0	B ₂ d d L d b g f d c Ldc Qg b - db
1.1/.1/1/	0-1	T. h f Qg b L h e H c Q ₂ L
7.5.1/10	0-2	T c Ldc e c 2 L f d. db - f d Qg b, h e c Ld b ₂ cd. ed 10/ 0 XXV V e L(